



Micro Commercial Components
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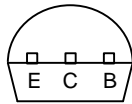
2SC2001

NPN Silicon Plastic-Encapsulate Transistor

Features

- Capable of 0.6Watts of Power Dissipation.
- Collector-current 0.7A
- Collector-base Voltage 30V
- Operating and storage junction temperature range: -55°C to +150°C

Pin Configuration
 Bottom View



Electrical Characteristics @ 25°C Unless Otherwise Specified

Symbol	Parameter	Min	Max	Units
OFF CHARACTERISTICS				
$V_{(BR)CEO}$	Collector-Emmitter Breakdown Voltage ($I_C=10\text{mAdc}$, $I_B=0$)	25	---	Vdc
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage ($I_C=100\mu\text{Adc}$, $I_E=0$)	30	---	Vdc
$V_{(BR)EBO}$	Emmitter-Base Breakdown Voltage ($I_E=100\mu\text{Adc}$, $I_C=0$)	5.0	---	Adc
I_{CBO}	Collector Cutoff Current ($V_{CB}=30\text{Vdc}$, $I_E=0$)	---	0.1	μAdc
I_{CEO}	Collector Cutoff Current ($V_{CE}=20\text{Vdc}$, $I_E=0$)	---	0.1	Vdc
I_{EBO}	Emmitter Cutoff Current ($V_{EB}=5.0\text{Vdc}$, $I_C=0$)	---	0.1	μAdc

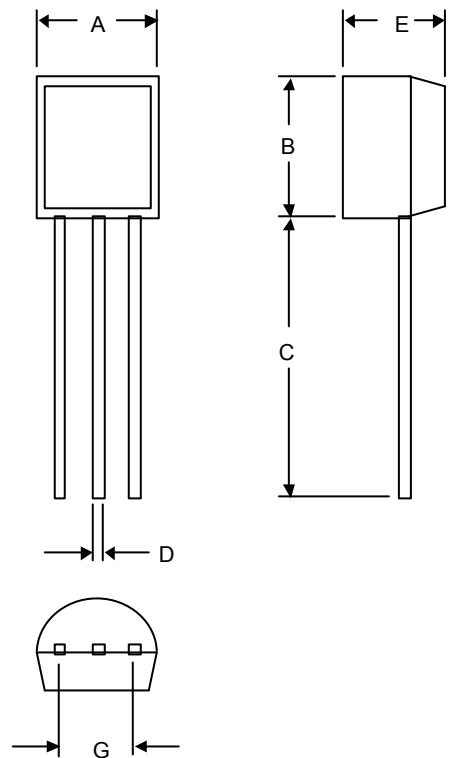
ON CHARACTERISTICS

h_{FE}	DC Current Gain ($I_C=100\text{mAdc}$, $V_{CE}=1.0\text{Vdc}$)	90	400	---
$V_{CE(sat)}$	Collector-Emmitter Saturation Voltage ($I_C=700\text{mAdc}$, $I_B=70\text{mAdc}$)	---	0.6	Vdc
$V_{(BE)sat}$	Base-Emmitter Saturation Voltage ($I_C=700\text{mAdc}$, $I_B=70\text{mAdc}$)	---	1.2	Vdc
fT	Transition Frequency ($V_{CE}=6.0\text{Vdc}$, $I_C=10\text{mAdc}$, $f=30\text{MHz}$)	50	---	MHz

CLASSIFICATION OF h_{FE}

Rank	M	L	K
Range	90-180	135-270	200-400

TO-92



DIM	INCHES		MM		NOTE
	MIN	MAX	MIN	MAX	
A	.175	.185	4.45	4.70	
B	.175	.185	4.46	4.70	
C	.500	---	12.7	---	
D	.016	.020	0.41	0.63	
E	.135	.145	3.43	3.68	
G	.095	.105	2.42	2.67	